



WM10N02M

N-Channel MOSFET

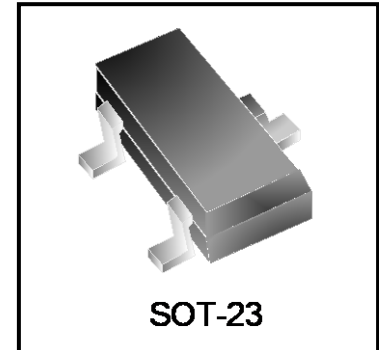
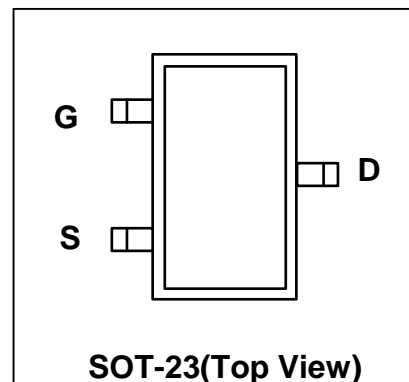
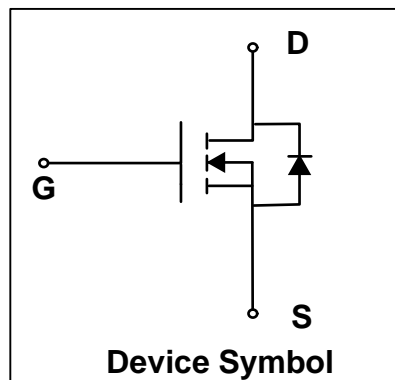
Features

- $V_{DS} = 100V$, $I_D = 0.2A$
 $R_{DS(on)} < 6\Omega @ V_{GS} = 10V$
 $R_{DS(on)} < 9\Omega @ V_{GS} = 4.5V$
- Switching Application
- Small Servo Motor Controls
- Rugged and Reliable

Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	0.2	A
Pulsed Drain Current ¹	I_{DM}	0.5	A
Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	357	$^{\circ}C/W$

Electrical Characteristics ($T_{amb}=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} = 0 V	-	-	1	μA
Gate-body Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20V	-	-	±1	μA
Gate Threshold Voltage ³	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	-	3	V
Drain-Source On-state Resistance ³	R _{DS(on)}	V _{GS} = 10V, I _D = 0.2A	-	3.5	6	Ω
		V _{GS} =4.5V, I _D = 0.17A	-	3.8	9	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz	-	25	-	pF
Output Capacitance	C _{oss}		-	3.6	-	
Reverse Transfer Capacitance	C _{rss}		-	1.5	-	
Switching Characteristics						
Total Gate Charge ⁴	Q _g	V _{GS} = 10V, V _{DS} = 10V, I _D = 0.2A	-	1.5	-	nC
Gate-Source Charge ⁴	Q _{gs}		-	0.18	-	
Gate-Drain Charge ⁴	Q _{gd}		-	0.22	-	
Turn-On Delay Time ⁴	t _{d(on)}	V _{DD} = 50V, V _{GS} =10V, I _D =0.2A, R _G = 6Ω	-	5.5	-	nS
Turn-On Rise Time ⁴	t _r			5.5		
Turn-Off Delay Time ⁴	t _{d(off)}		-	7.8	-	
Turn- Off Fall Time ⁴	t _f		-	10	-	
Source-Drain Diode Characteristics						
Body Diode Voltage	V _{SD}	I _S = 0.2A, V _{GS} = 0V	-	-	1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface mounted on FR4 board using 1 square inch pad size, 1oz single-side copper.
3. Pulse Test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product

Typical Characteristics

Figure 1. Output Characteristics

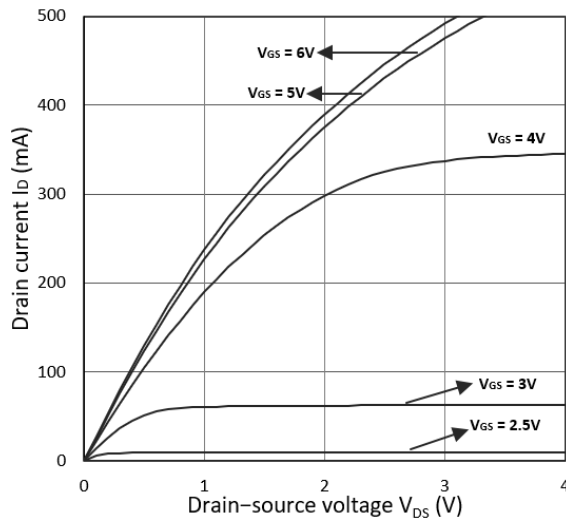


Figure 2. Transfer Characteristics

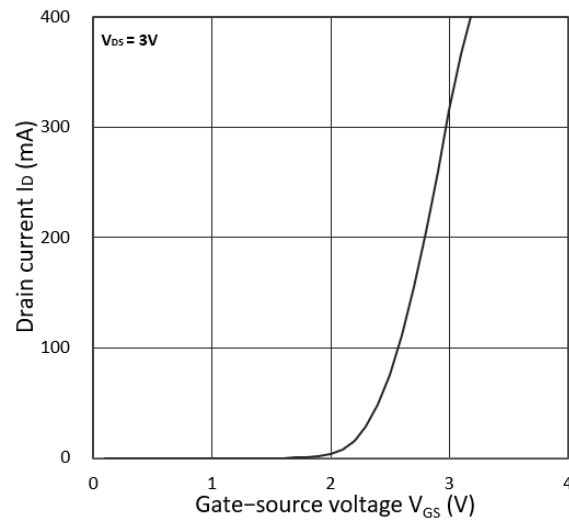
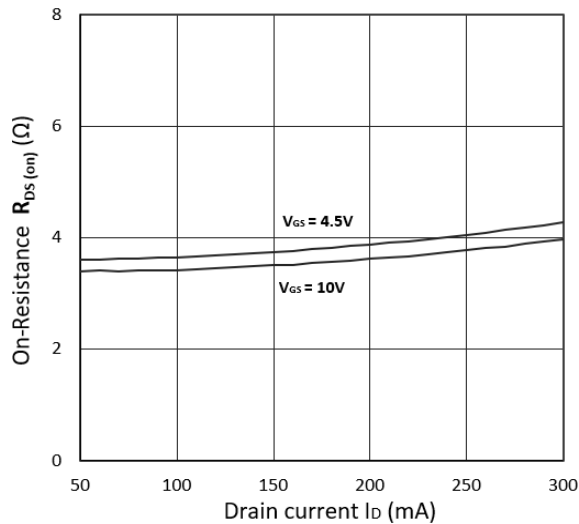
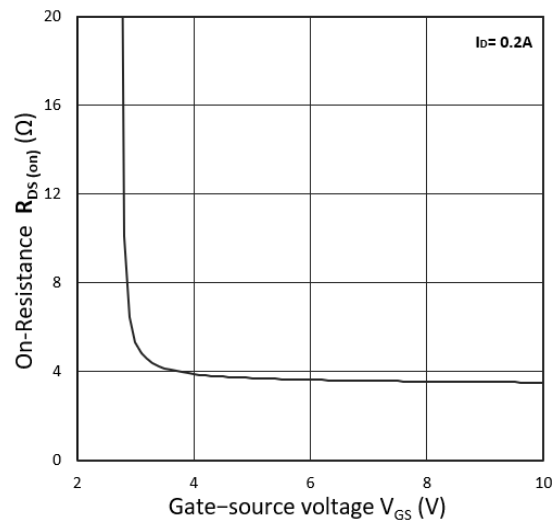
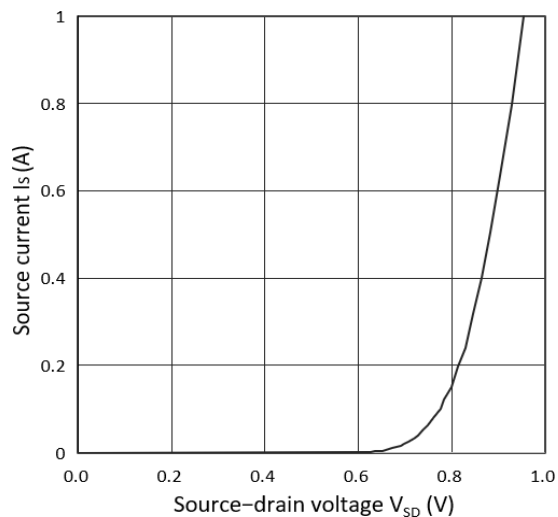
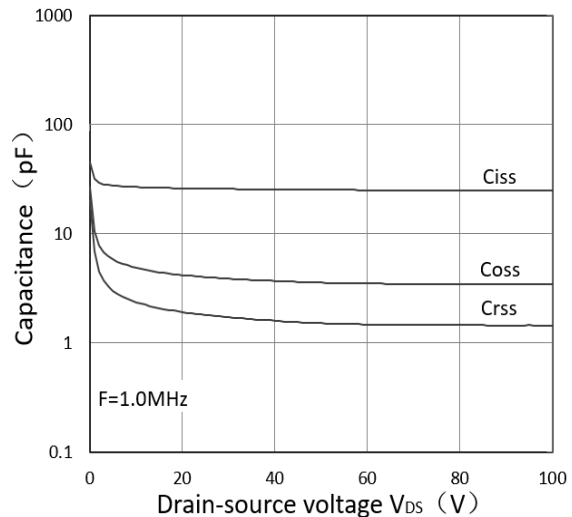
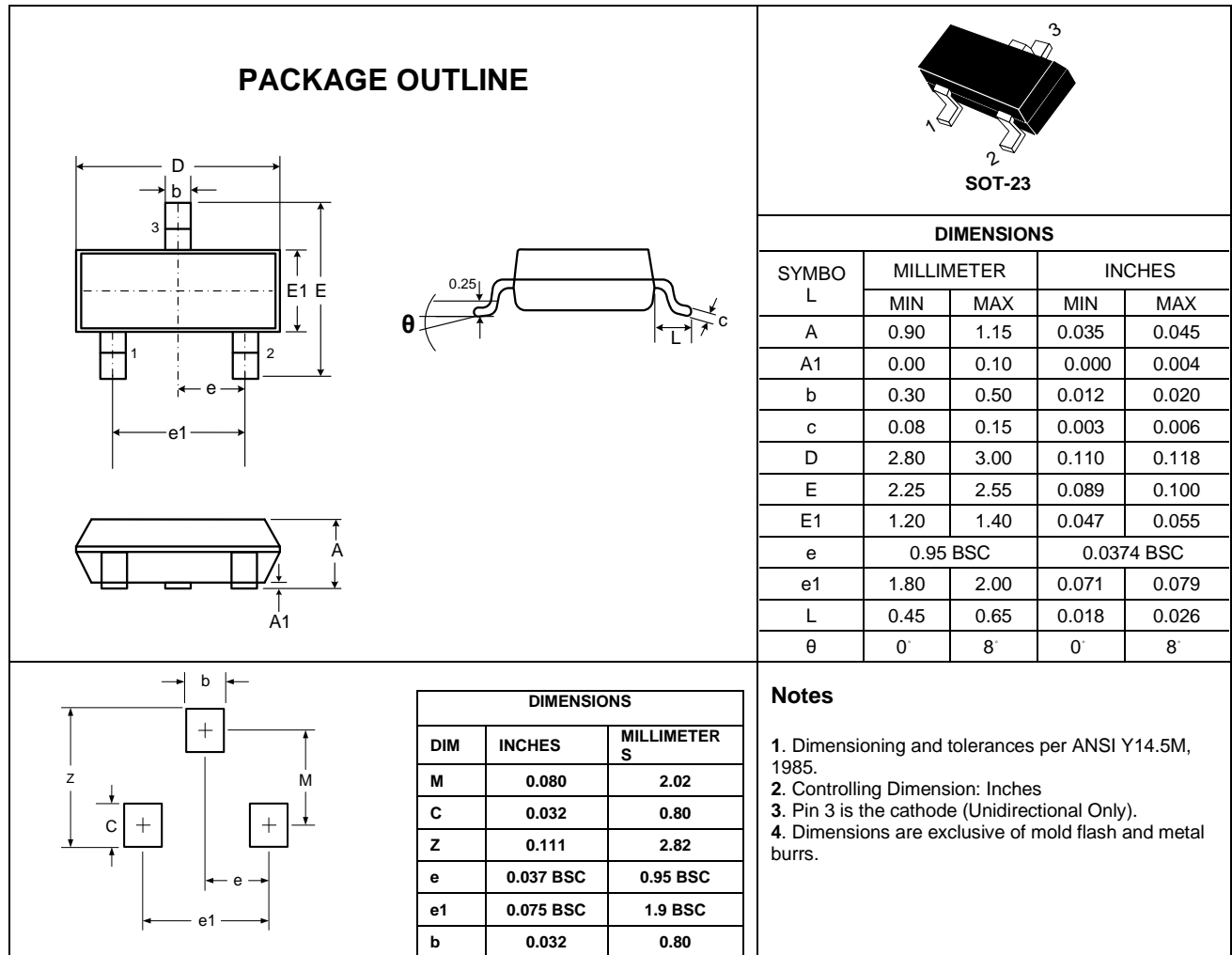
Figure 3. $R_{DS(ON)}$ vs. I_D Figure 4. $R_{DS(ON)}$ vs. V_{GS} Figure 5. I_S vs. V_{SD} 

Figure 6. Capacitance Characteristics



Outline Drawing – SOT-23



Marking Codes

Part Number	WM10N02M
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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For additional information, please contact your local Sales Representative.

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